Automotive MOSFET

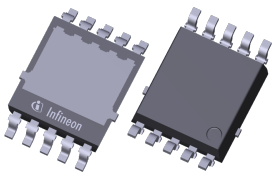
OptiMOS™ 7 Power-Transistor

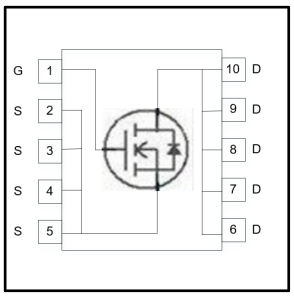
RoHS | Infineon Automotive Quality | AEC Qualified

Features

- OptiMOS™ power MOSFET for automotive applications
- N-channel - Enhancement mode - Normal Level
- Extended qualification beyond AEC-Q101
- Enhanced electrical testing
- Robust design
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- RoHS compliant
- 100% Avalanche tested

PG-LHDSO-10-2





Potential Applications

General automotive applications.

Product Validation

Qualified for automotive applications. Product validation according to AEC-Q101.

Product Summary

V_{DS}	80	V
$R_{DS(on)}$	1.94	mΩ
I_D (chip limited)	223	A

Type	Package	Marking
IAUCN08S7N019T	PG-LHDSO-10-2	7B8

Table of Contents

Maximum Ratings

at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	V_{GS} = 10 V, Chip limitation[1,2)]	223	A
		V_{GS} = 10 V, DC current	175	
		T_a = 100°C, V_{GS} = 10 V, R_{thJH} on 2s2p[2,4)]	51	
Pulsed drain current[2)]	$I_{D,pulse}$	T_C = 25°C, t_p = 100 µs	630	
Avalanche energy, single pulse[2)]	E_{AS}	I_D = 66 A	155	mJ
Avalanche current, single pulse	I_{AS}	–	132	A
Gate source voltage	V_{GS}	–	±20	V
Power dissipation	P_{tot}	T_C = 25°C	180	W
Operating and storage temperature	T_j, T_{stg}	–	-55 ... +175	°C

Thermal Characteristics[2)]

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	–	–	0.42	0.83	K/W
Thermal characterisation parameter, source pin[5)]	Ψ_{source}	–	–	5.3	–	
Thermal characterisation parameter, drain pin[6)]	Ψ_{drain}	–	–	5.4	–	
Thermal resistance, junction - heatsink[4)]	R_{thJH}	–	–	6.9	–	
Thermal resistance, junction - ambient[3)]	R_{thJA}	–	–	49	–	

Electrical Characteristics

at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Static Characteristics						
Drain-source breakdown voltage	$V_{(Br)DSS}$	V_{GS} = 0 V, I_D = 1 mA	80	–	–	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 93.4 µA	2.3	2.8	3.2	
Zero gate voltage drain current	I_{DSS}	V_{DS} = 80 V, V_{GS} = 0 V, T_j = 25°C	–	–	1	µA
		V_{DS} = 80 V, V_{GS} = 0 V, T_j = 100°C[2)]	–	–	100	
Gate-source leakage current	I_{GSS}	V_{GS} = 20 V, V_{DS} = 0 V	–	–	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 7 V, I_D = 44 A	–	2.00	2.27	mΩ
		V_{GS} = 10 V, I_D = 88 A	–	1.78	1.94	
Gate resistance[2)]	R_G	–	–	0.84	–	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic Characteristics[2]						
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 40 V, f = 1 MHz	–	4662	6061	pF
Output capacitance	C_{oss}		–	1889	2456	
Reverse transfer capacitance	C_{rss}		–	23	35	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 40 V, V_{GS} = 10 V, I_D = 88 A, R_G = 3.5 Ω	–	14	–	ns
Rise time	t_r		–	16	–	
Turn-off delay time	$t_{d(off)}$		–	27	–	
Fall time	t_f		–	17	–	
Gate Charge Characteristics[2]						
Gate to source charge	Q_{gs}	V_{DD} = 40 V, I_D = 88 A, V_{GS} = 0 to 10 V	–	22	28	nC
Gate to drain charge	Q_{gd}		–	13	18	
Gate charge total	Q_g		–	68	88	
Gate plateau voltage	$V_{plateau}$		–	4.6	–	V
Reverse Diode						
Diode continuous forward current[2]	I_S	T_C = 25°C	–	–	175	A
Diode pulse current[2]	$I_{S,pulse}$	T_C = 25°C, t_p = 100 µs	–	–	630	
Diode forward voltage	V_{SD}	V_{GS} = 0 V, I_F = 88 A, T_j = 25°C	–	0.9	1.0	V
Reverse recovery time[2]	t_{rr}	V_R = 40 V, I_F = 50 A, di_F/dt = 100 A/µs	–	41	61	ns
Reverse recovery charge[2]	Q_{rr}		–	31	61	nC

[1] Practically the current is limited by the overall system design including the customer-specific PCB.

[2] The parameter is not subject to production testing – specified by design.

[3] Device on 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5, -7) without thermal vias, heatsink of 71x110x2 mm is attached through TIM with 3.3 W/(m*K) and 400µm thickness to top side pad. Heatsink fixed to 85°C ambient temperature.

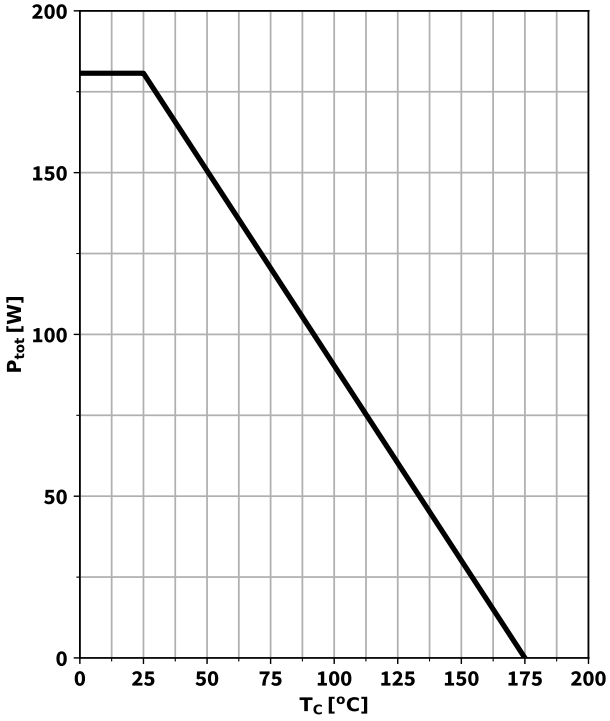
[4] Thermal characterization parameter, calculated as $\psi_{source} = (T_{source} - T_{ambient})/P_{dis}$ in condition of 4). Used to determine PCB temperature at source pins for given power.

[5] Thermal characterization parameter, calculated as $\psi_{drain} = (T_{drain} - T_{ambient})/P_{dis}$ in condition of 4). Used to determine PCB temperature at drain pins for given power.

Electrical characteristics diagrams

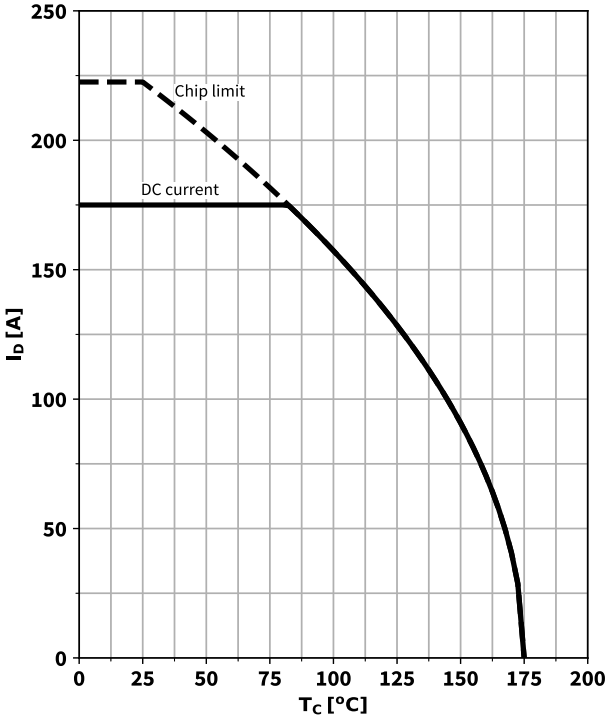
1 Power dissipation

$P_{tot} = f(T_C)$; $V_{GS} \geq 6$ V



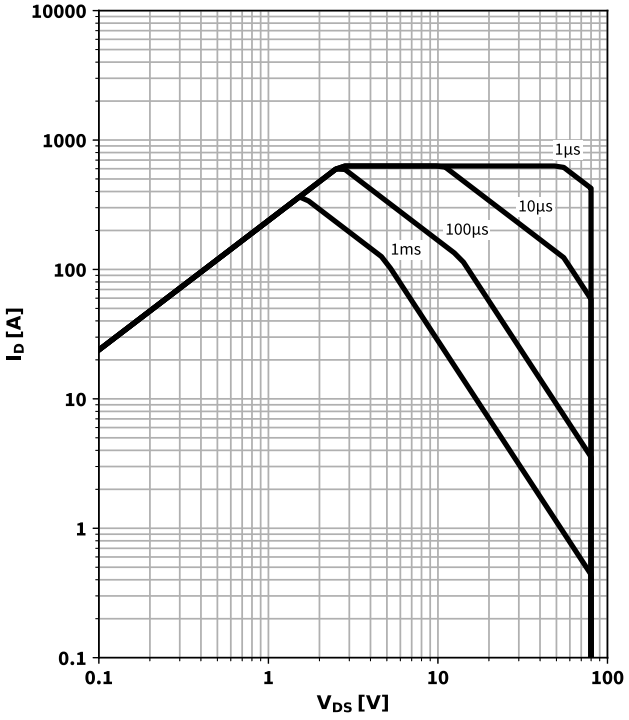
2 Drain current

$I_D = f(T_C)$; $V_{GS} \geq 6$ V



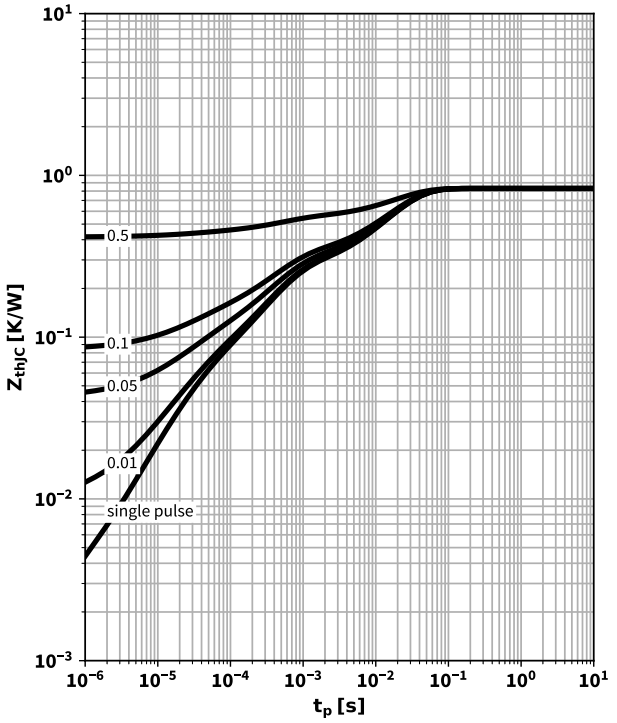
3 Safe operating area

$I_D = f(V_{DS})$; $T_C = 25$ °C; $D = 0$; parameter: t_p



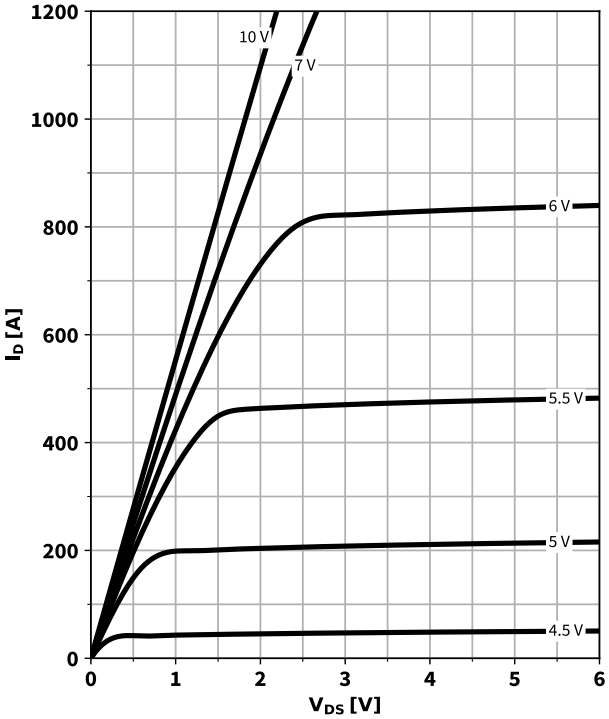
4 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$; parameter: $D = t_p/T$



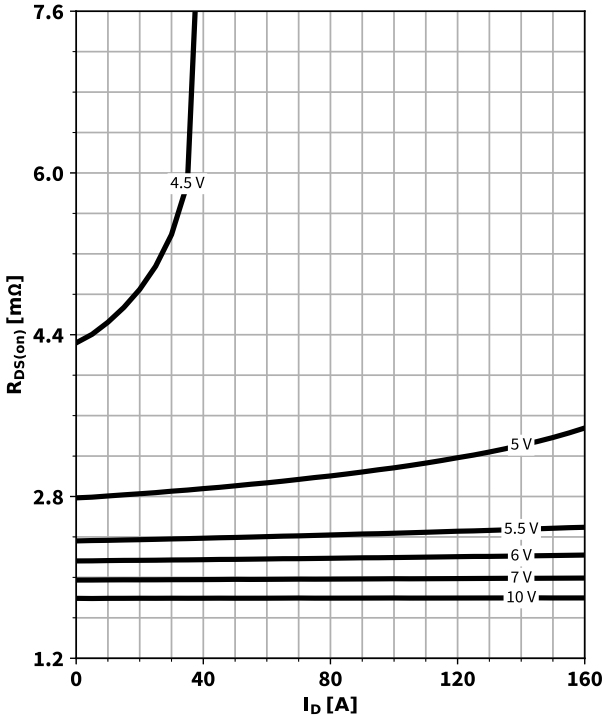
5 Typ. output characteristics

$I_D = f(V_{DS})$; $T_j = 25$ °C; parameter: V_{GS}



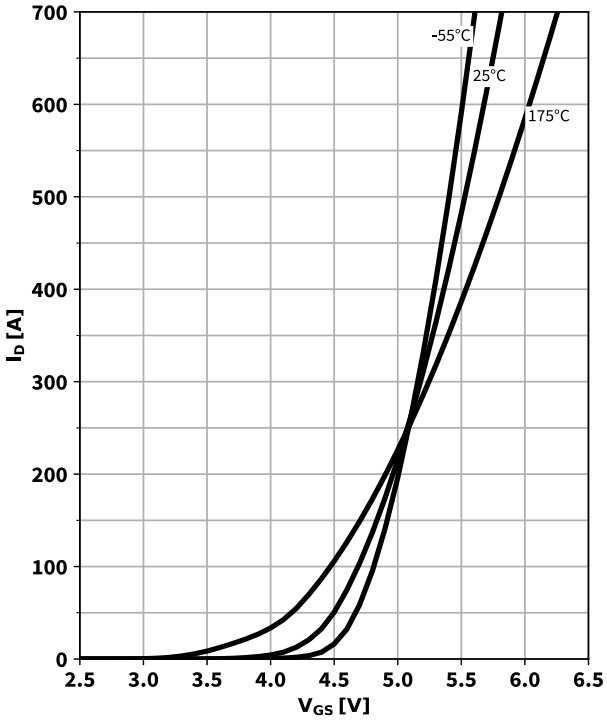
6 Typ. drain-source on-state resistance

$R_{DS(on)} = f(I_D)$; $T_j = 25$ °C; parameter: V_{GS}



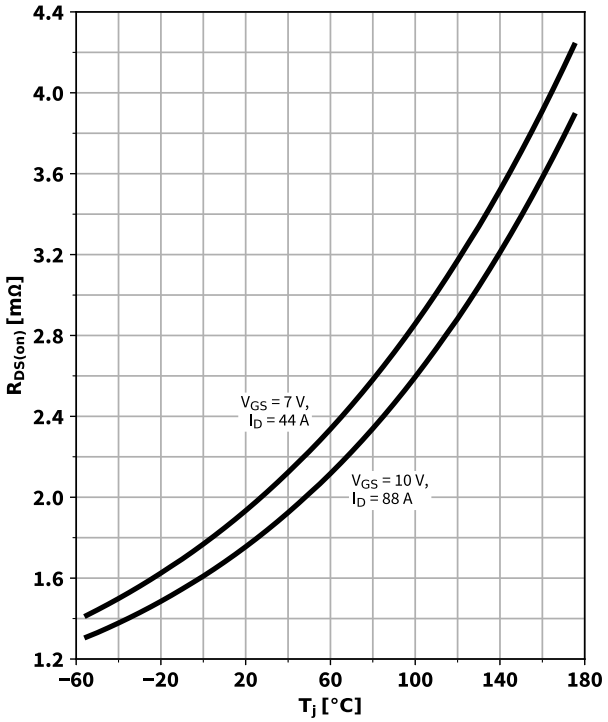
7 Typ. transfer characteristics

$I_D = f(V_{GS})$; $V_{DS} = 6$ V; parameter: T_j



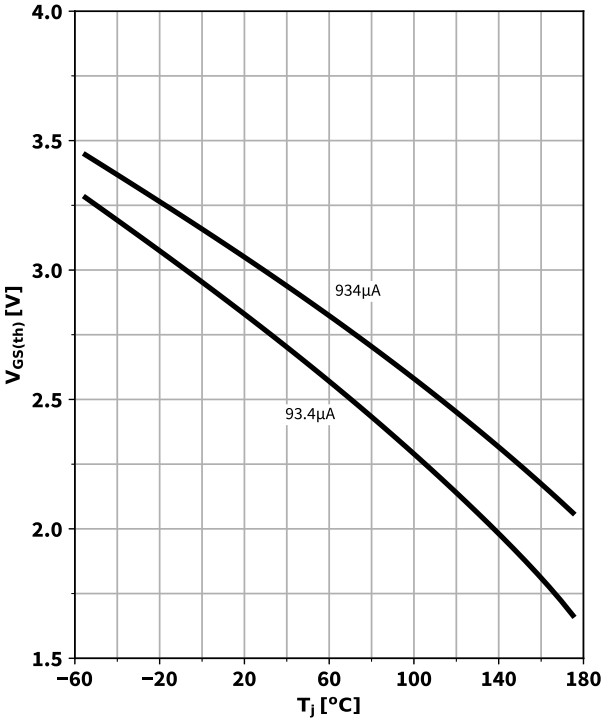
8 Typ. drain-source on-state resistance

$R_{DS(on)} = f(T_j)$; parameter: I_D, V_{GS}



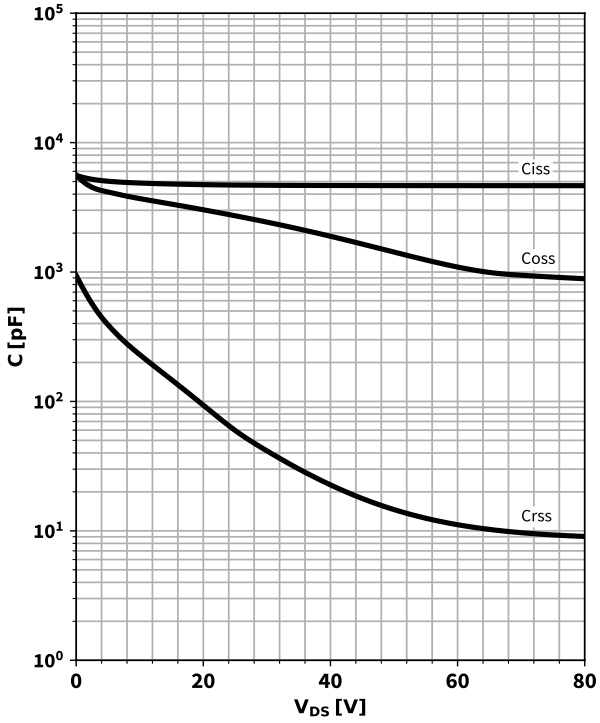
9 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$; parameter: I_D



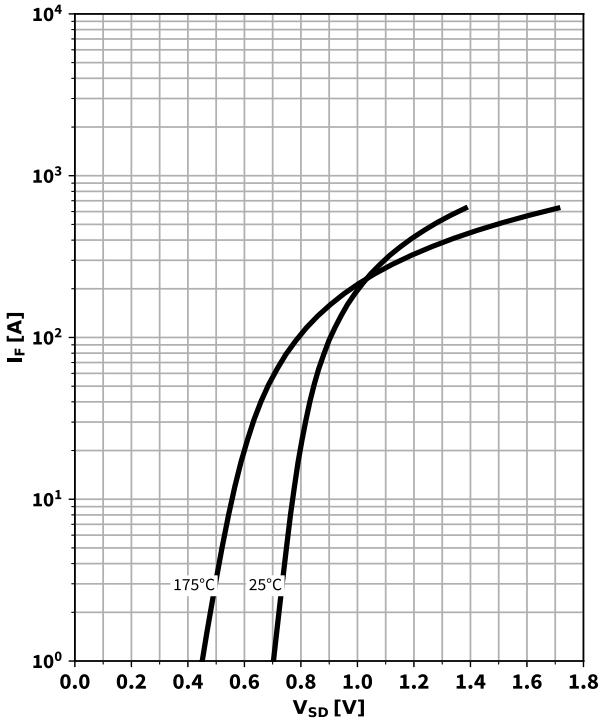
10 Typ. capacitances

$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz



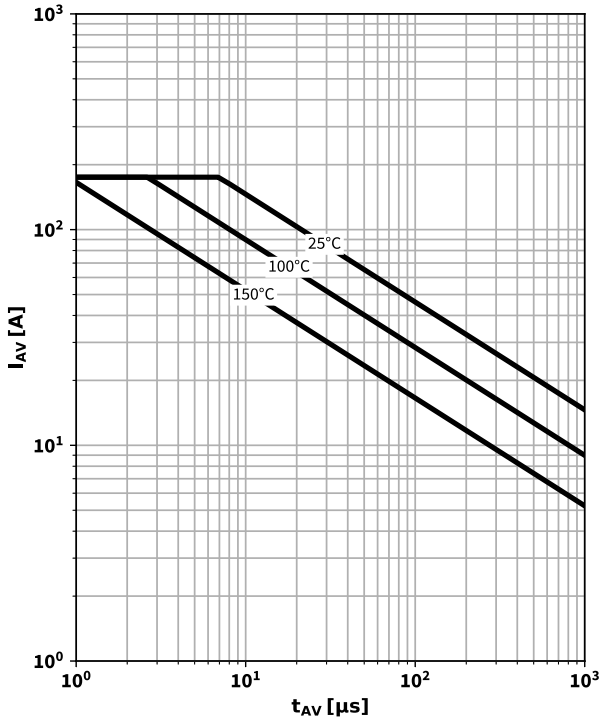
11 Typ. forward diode characteristics

$I_F = f(V_{SD})$; parameter: T_j



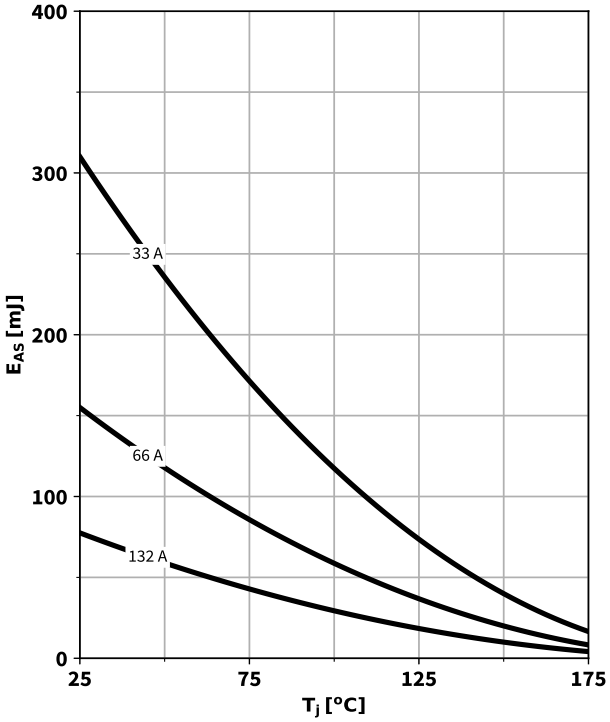
12 Typ. avalanche characteristics

$I_{AS} = f(t_{AV})$; parameter: $T_{j(start)}$



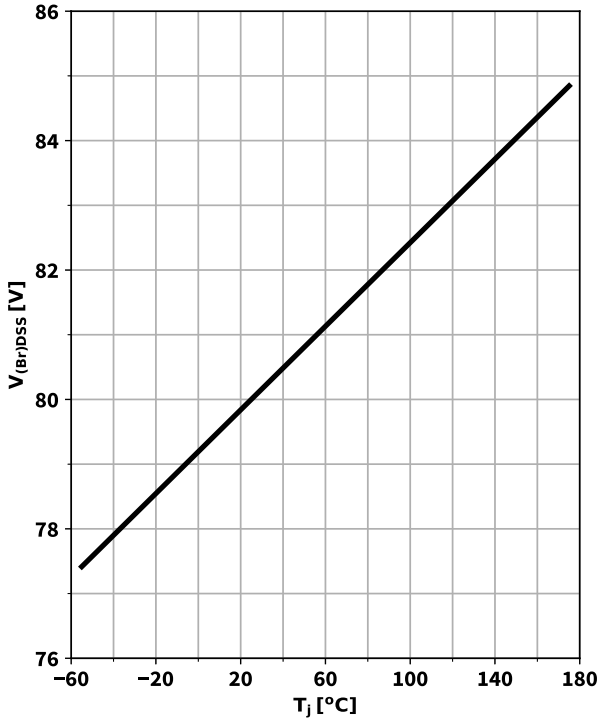
13 Typical avalanche energy

$E_{AS} = f(T_j)$; parameter: I_D



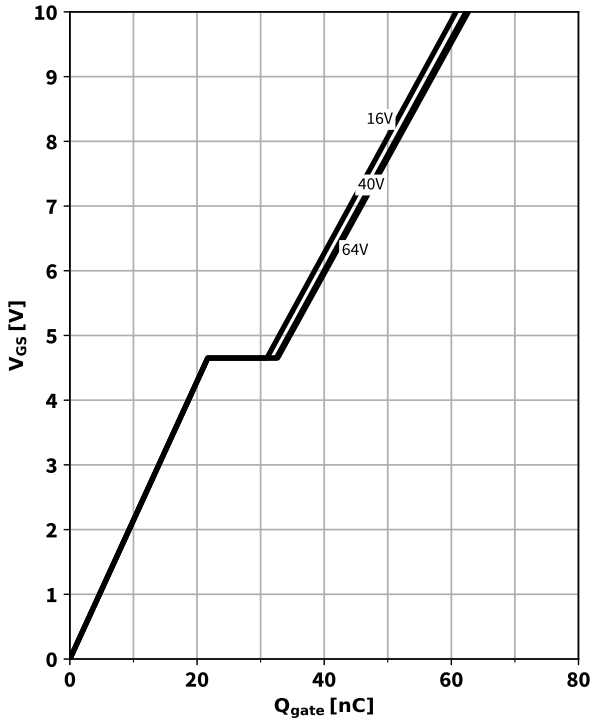
14 Drain-source breakdown voltage

$V_{(Br)DSS} = f(T_j)$; I_D = 1 mA

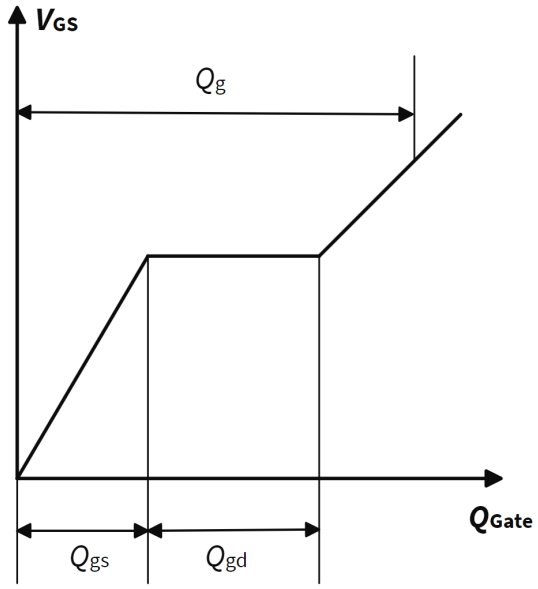


15 Typ. gate charge

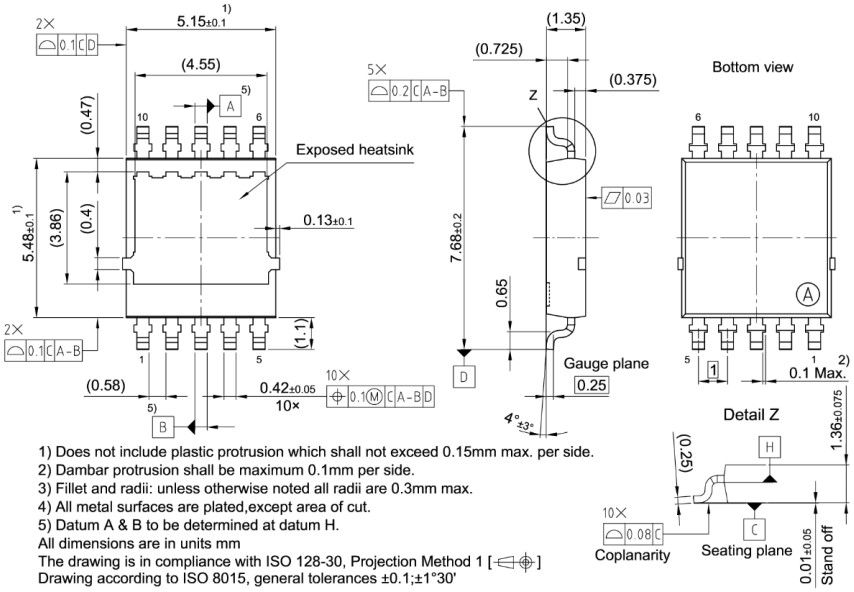
$V_{GS} = f(Q_{gate})$; I_D = 88 A pulsed; parameter: V_{DD}



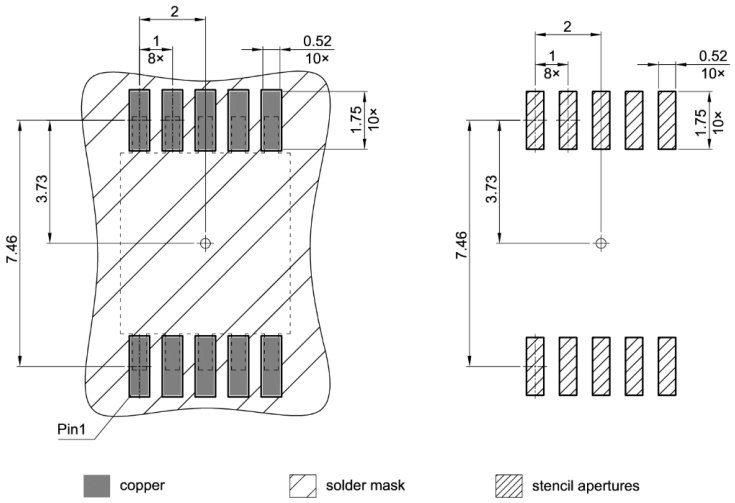
16 Gate charge waveforms



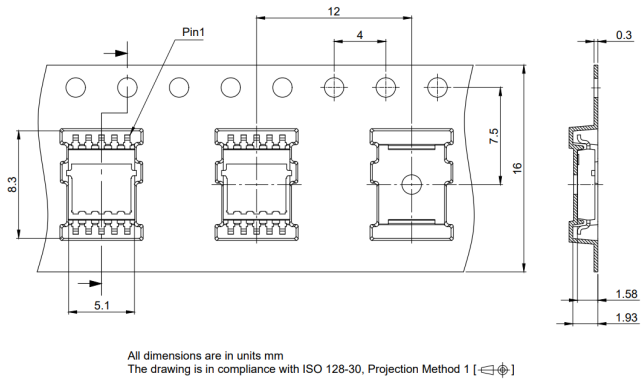
Package Outline



Footprint



Packaging



Revision History

Revision	Date	Changes
Revision 1.0	11.11.2024	Final data sheet

Trademarks
All referenced product or service names and trademarks are the property of their respective owners.

Edition 2024

Published by

Infineon Technologies AG

81726 Munich, Germany

Do you have any questions about any aspect of this document?

Email: erratum@infineon.com

Document reference
IAUCN08S7N019T-Data-Sheet-10-Infineon

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications. The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (**www.infineon.com**).

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact the nearest Infineon Technologies Office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.